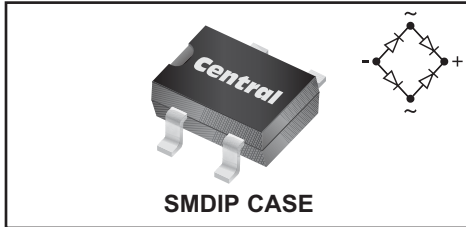


CBR1F-D020S SERIES**SURFACE MOUNT
1 AMP FAST RECOVERY
SILICON BRIDGE RECTIFIER**www.centrasemi.com**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBR1F-D020S Series types are fast recovery, full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER**MAXIMUM RATINGS:**(T_A=25°C unless otherwise specified)

	SYMBOL	CBR1F-D020S	CBR1F-D040S	CBR1F-D060S	CBR1F-D080S	CBR1F-D100S	UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V _R	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	560	700	V
Average Forward Current (T _A =40°C)	I _O			1.0			A
Peak Forward Surge Current	I _{FSM}			50			A
Rating for Fusing (t<8.35ms)	I ² t			3.74			A ² s
Operating and Storage Junction Temperature	T _J , T _{stg}			-65 to +150			°C

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I _R	V _R =Rated V _{RRM}		5.0	µA
I _R	V _R =Rated V _{RRM} , T _A =125°C		0.5	mA
V _F	I _F =1.0A		1.3	V
t _{rr}	I _F =0.5A, I _R =1.0A, Rec. to 0.25A (200V, 300V, 400V)		200	ns
t _{rr}	I _F =0.5A, I _R =1.0A, Rec. to 0.25A (600V)		300	ns
t _{rr}	I _F =0.5A, I _R =1.0A, Rec. to 0.25A (800V, 1000V)		500	ns
C _J	V _R =4.0V, f=1.0MHz	25		pF

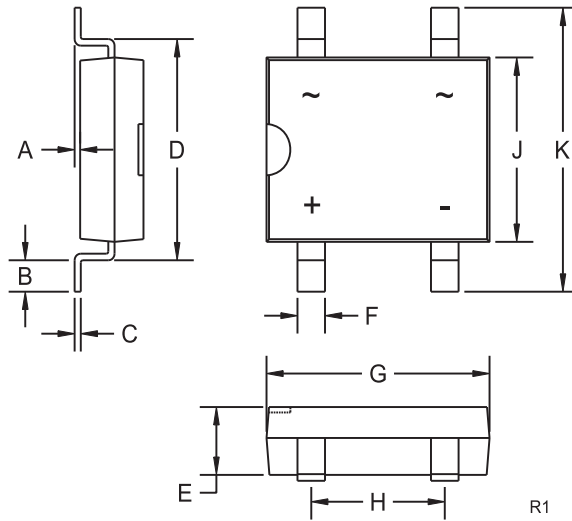
R1 (4-January 2010)

CBR1F-D020S SERIES

**SURFACE MOUNT
1 AMP FAST RECOVERY
SILICON BRIDGE RECTIFIER**



SMDIP CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R1 (4-January 2010)